

METHOD FOR MANUFACTURING SEMICONDUCTOR CHIP

ABSTRACT

A semiconductor wafer (1) being exposed at street parts is etched by irradiating SF_6 gas plasma from a front surface side thereof and then separated into individual semiconductor chips (7). Next, a peeling tape (16) is pasted onto a top surface side of a mask material layer (3b). The peeling tape (16) is formed of a substrate film 16a on which an adhesive layer 16b is provided. After pasting and curing the peeling tape (16), the peeling tape (16) is peeled off together with the mask material layer (3b). That is, the mask material layer (3b) is adhered to the peeling tape (16), and the mask material layer (3b) is peeled off from a patterned surface (2).

[FIG. 5C]